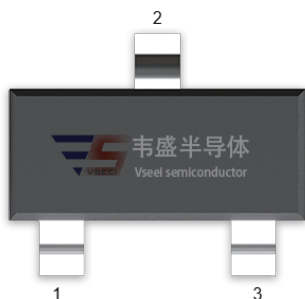
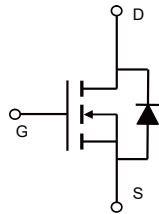


Description

Features 20V, 8A $R_{DS(ON)} < 10.7m\Omega @ V_{GS} = 4.5V$ $R_{DS(ON)} < 13.3m\Omega @ V_{GS} = 2.5V$ - Advanced Trench Technology - Excellent $R_{DS(ON)}$ and Low Gate Charge - Lead Free	Applications - Load Switch - PWM Application - Power Management
 SOT-23-3	 Schematic

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel(pcs)	Per Carton (pcs)
VSM100N02A	VSM100N02A-S2-3	TAPING	SOT-23-3	7"	3000	120000

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	A
		$T_A = 100^\circ C$	
I_{DM}	Pulsed Drain Current ⁽¹⁾	32	A
P_D	Power Dissipation	$T_A = 25^\circ C$	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	92	$^\circ C/W$
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ C$

Electrical Characteristics ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0V	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 20V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	0.4	0.8	1.0	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 4.5V, I _D = 15A	-	8.2	10.7	m Ω
		V _{GS} = 2.5V, I _D = 10A	-	10.2	13.3	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz	-	1195	-	pF
C _{oss}	Output Capacitance		-	175	-	pF
C _{rss}	Reverse Transfer Capacitance		-	150	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 4.5V V _{DS} = 10V, I _D = 15A	-	13	-	nC
Q _{gs}	Gate Source Charge		-	2.5	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	3.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 4.5V, V _{DD} = 10V I _D = 15A, R _{GEN} = 3 Ω	-	7.5	-	ns
t _r	Turn-On Rise Time		-	18.9	-	ns
t _{d(off)}	Turn-Off DelayTime		-	30.4	-	ns
t _f	Turn-Off Fall Time		-	11.2	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 8A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 15A, di/dt = 100A/us	-	7.5	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	1.5	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Output Characteristics

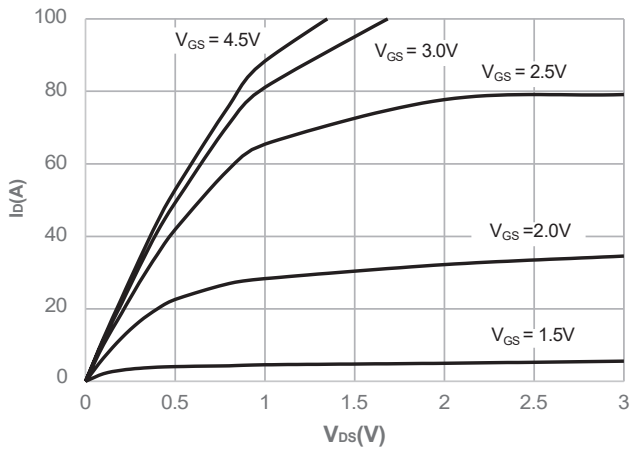


Figure 2: Typical Transfer Characteristics

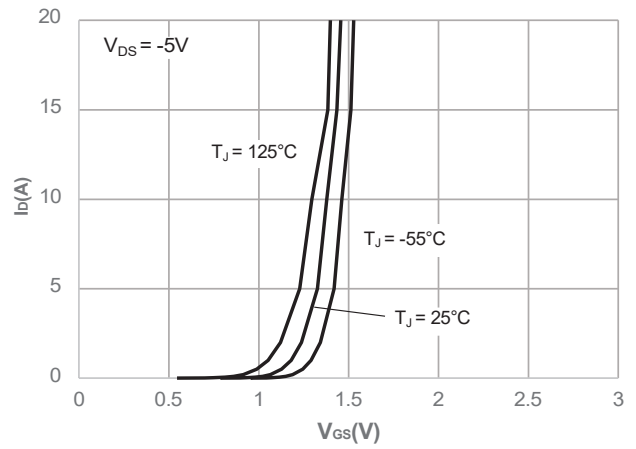


Figure 3: On-resistance vs. Drain Current

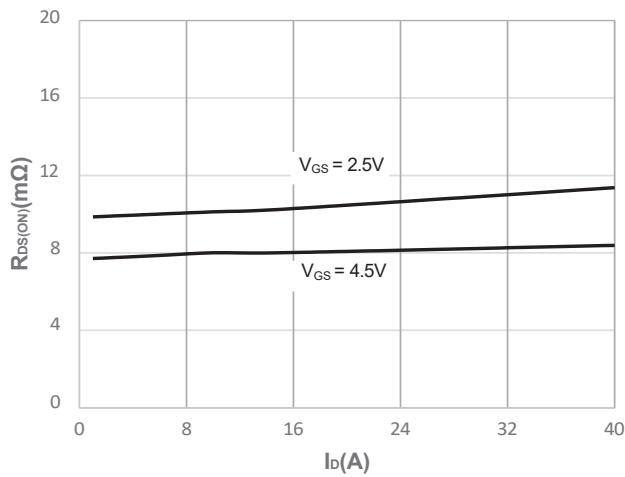


Figure 4: Body Diode Characteristics

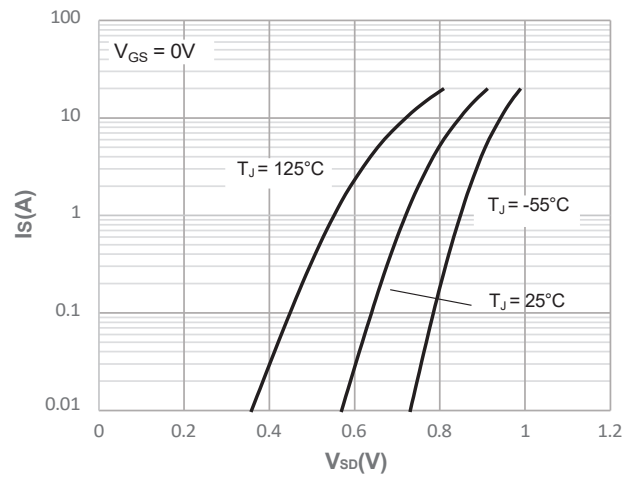


Figure 5: Gate Charge Characteristics

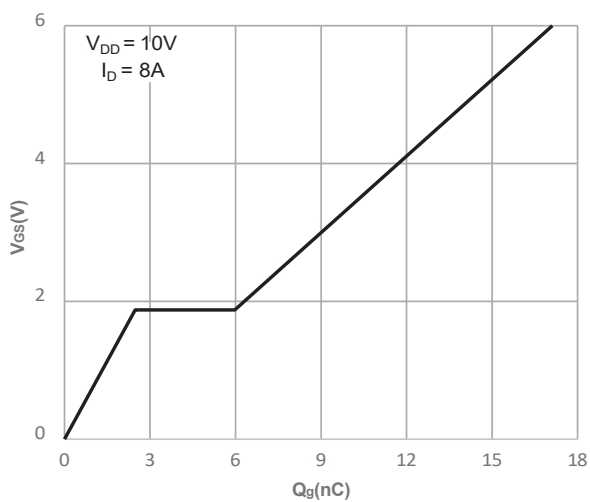
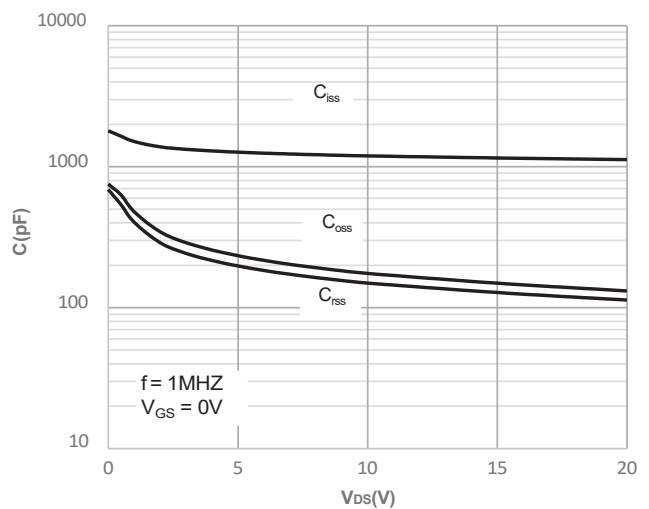


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

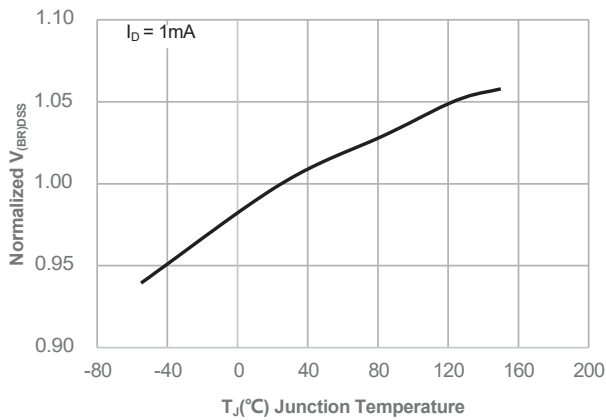


Figure 8: Normalized on Resistance vs. Junction Temperature

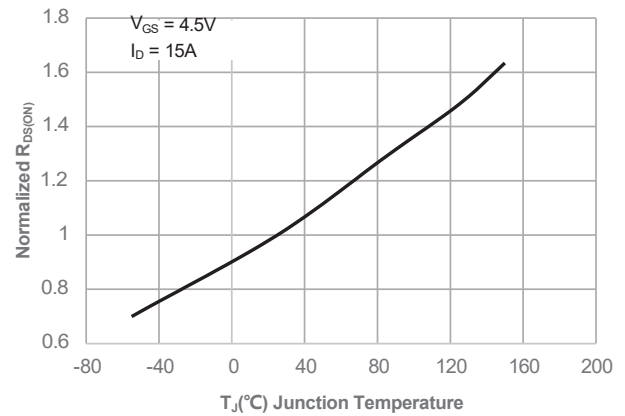


Figure 9: Maximum Safe Operating Area

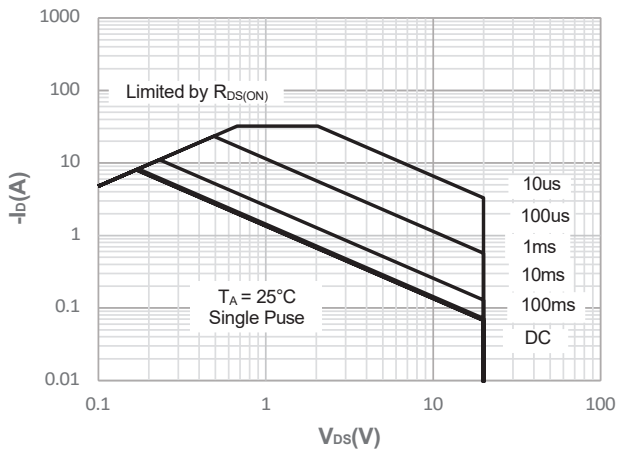


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

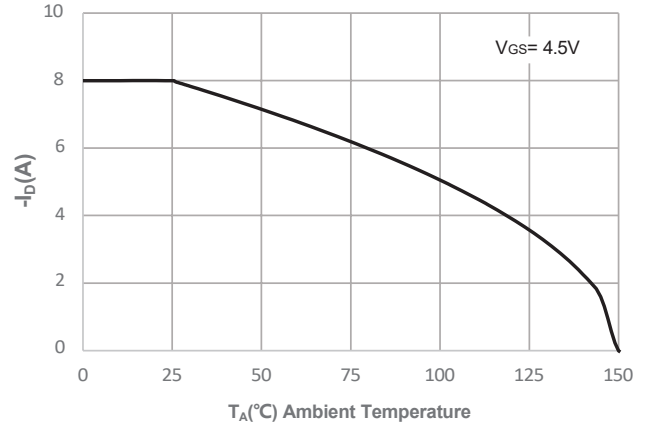


Figure 11: Normalized Maximum Transient Thermal Impedance

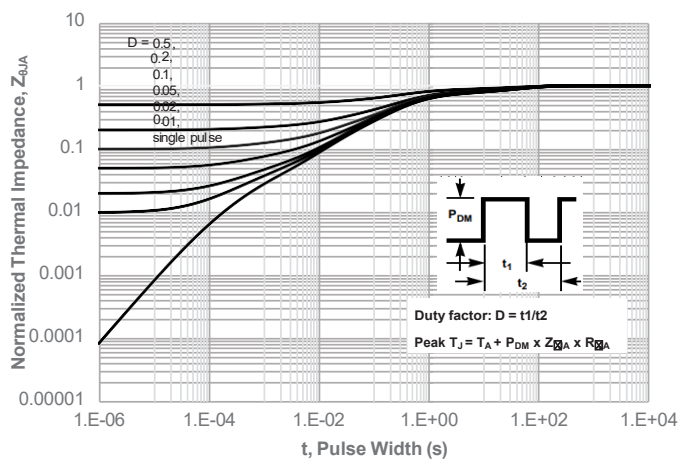
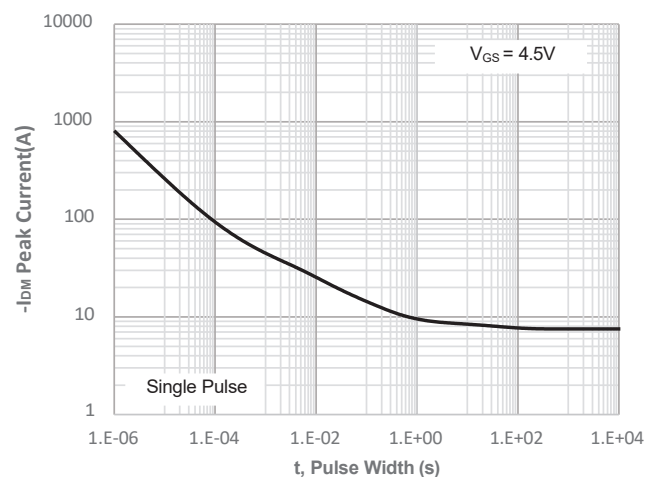


Figure 12: Peak Current Capacity



Test Circuit

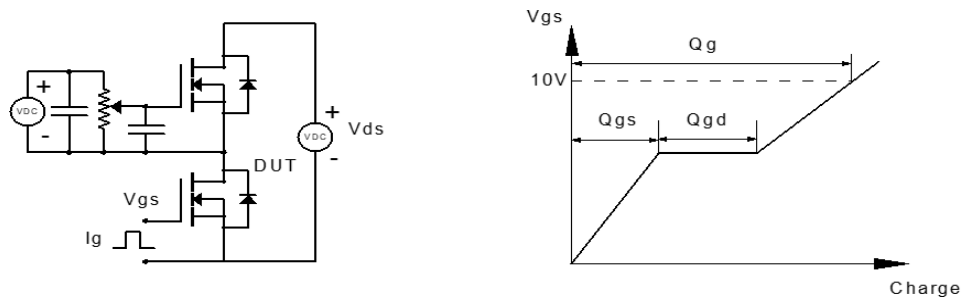


Figure 1: Gate Charge Test Circuit & Waveform

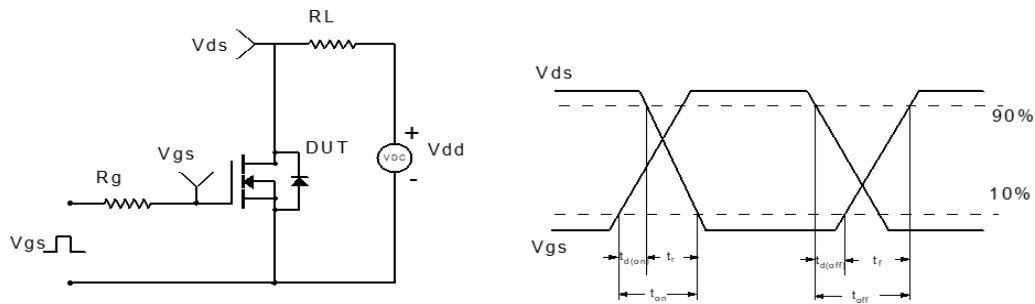


Figure 2: Resistive Switching Test Circuit & Waveform

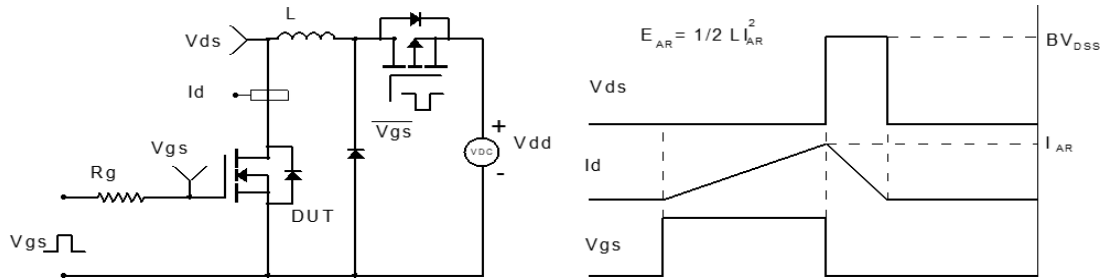


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

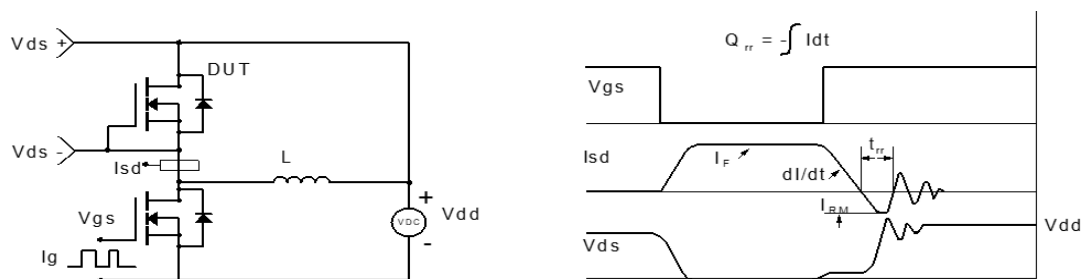


Figure 4: Diode Recovery Test Circuit & Waveform